# 2SB1416

# Silicon PNP epitaxial planar type

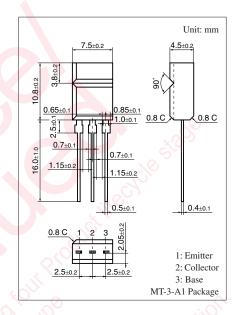
For low-frequency power amplification Complementary to 2SD2136

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub> which has satisfactory linearity
- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- Allowing automatic insertion with radial taping

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	-60	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-60	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V	
Collector current	$I_{C}$	-3	A	
Peak collector current	$I_{CP}$	-5	A	
Collector power dissipation	P <sub>C</sub>	1.5	W	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



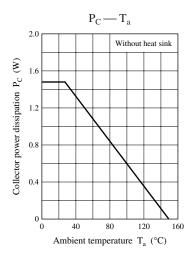
### ■ Electrical Characteristics T<sub>a</sub> = 25°C ± 3°C

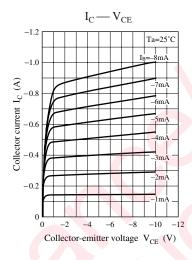
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = -30 \text{ mA}, I_B = 0$	-60			V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -4 \text{ V}, I_{C} = -3 \text{ A}$	7.9		-1.8	V
Collector-emitter cutoff current (E-B short)	I <sub>CES</sub>	$V_{CE} = -60 \text{ V}, V_{BE} = 0$			-200	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -30 \text{ V}, I_B = 0$			-300	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-1	mA
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -4 \text{ V}, I_{C} = -1 \text{ A}$	40		250	_
	h <sub>FE2</sub>	$V_{CE} = -4 \text{ V}, I_C = -3 \text{ A}$	10			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -3 A, I_B = -0.375A$			-1.2	V
Transition frequency	$f_T$	$V_{CB} = -5 \text{ V}, I_E = 0.1 \text{ A}, f = 200 \text{ MHz}$		270		MHz
Turn-on time	t <sub>on</sub>	$I_C = -1 A$ , $I_{B1} = -0.1 A$ , $I_{B2} = 0.1 A$		0.5		μs
Storage time	t <sub>stg</sub>			1.2		μs
Fall time	t <sub>f</sub>			0.3		μs

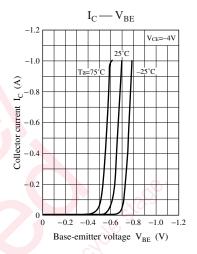
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

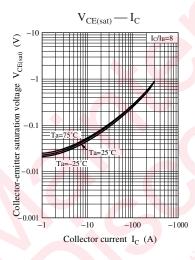
#### 2. \*: Rank classification

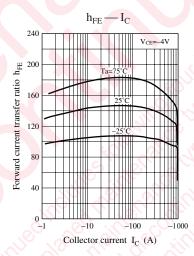
Rank	Р	Q	R
h <sub>FE1</sub>	40 to 90	70 to 150	120 to 250

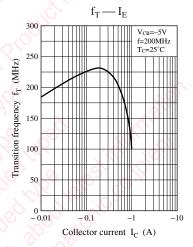


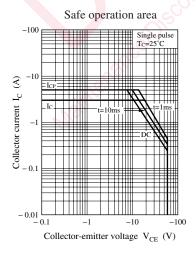


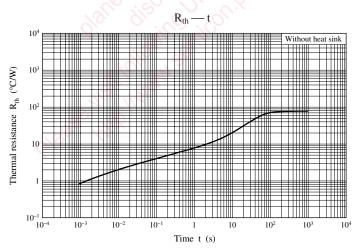












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